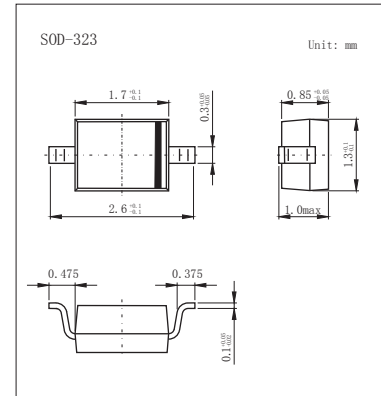


Switching Diodes

BAS16H

■ Features

- High speed switching
- High reliability

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_{RM}	90	V
Reverse Voltage (DC)	V_R	80	
Average Rectified Forward Current	I_o	100	mA
Peak Forward Surge Current	I_{FM}	225	
Surge Current ($t=1s$)	I_{Surge}	500	
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu\text{A}$	80			V
Forward voltage	V_F	$I_F = 100 \text{ mA}$			1.2	
Reverse voltage leakage current	I_R	$V_R = 80 \text{ V}$			0.1	μA
Capacitance between terminals	C_t	$V_R = 0.5 \text{ V}, f = 1 \text{ MHz}$			3	pF
Reverse recovery time	t_{rr}	$V_R = 6 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$			4	ns

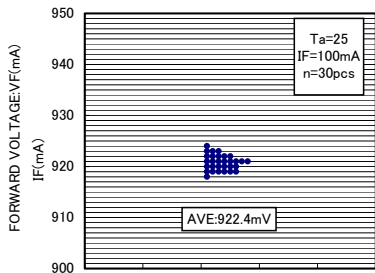
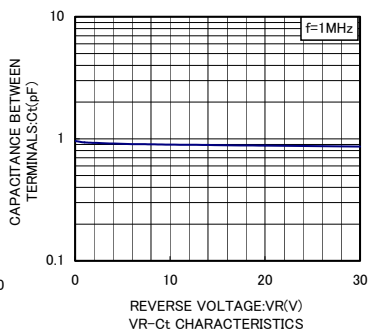
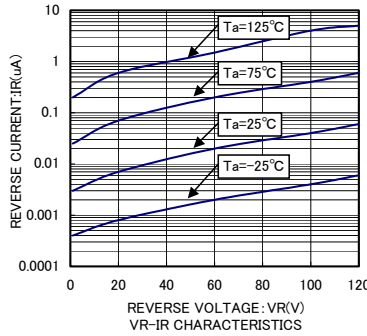
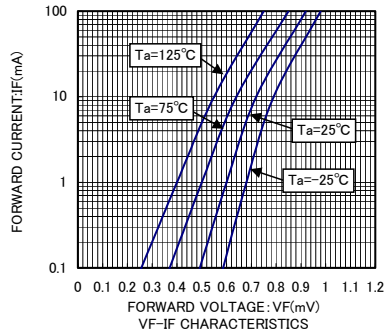
■ Marking

Marking	A
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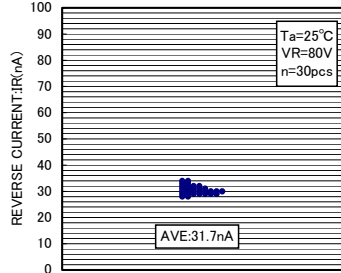
Switching Diodes

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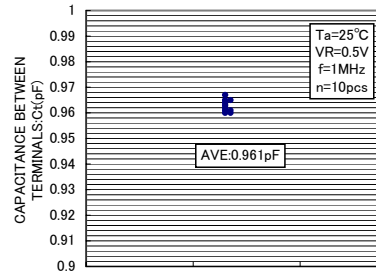
Typical Characteristics



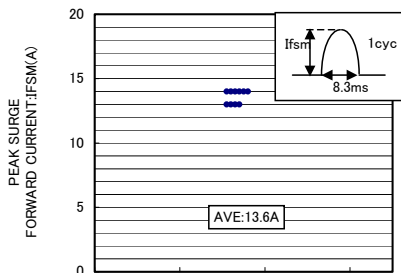
VF DISPERSION MAP



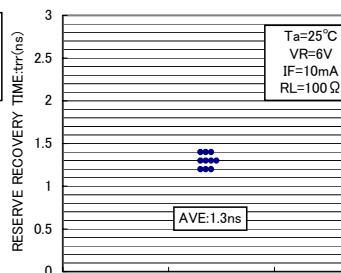
IR DISPERSION MAP



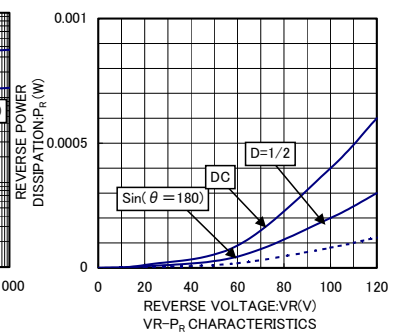
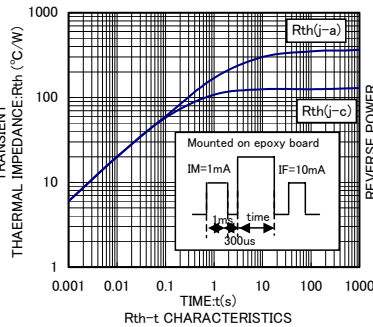
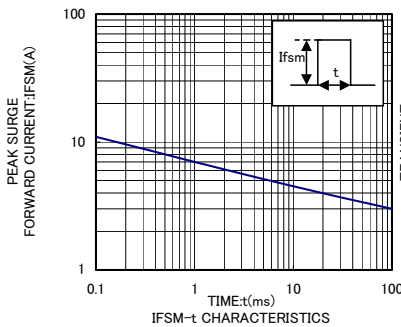
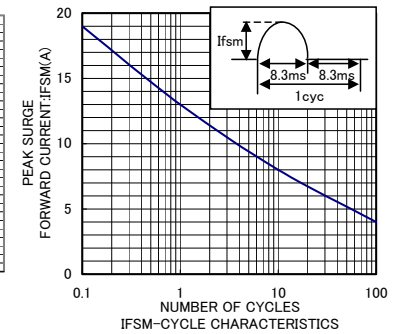
C_t DISPERSION MAP



IFSM DISRESION MAP



t_{rr} DISPERSION MAP



Switching Diodes

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■ Typical Characteristics

